



## **Fast Infrared Transceiver Module Family (FIR, 4 Mbit/s) for 2.6 V to 5.5 V Operation**



### **Description**

The TFDU6102E, TFDS6402, TFDS6502E, TFDT6502E are a family of low-power infrared transceiver modules compliant to the IrDA physical layer standard for fast infrared data communication, supporting IrDA speeds up to 4.0 Mbit/s (FIR), HP-SIR, Sharp ASK and carrier based remote control modes up to 2 MHz. Integrated within the transceiver modules are a photo PIN diode, an infrared emitter (IRED), and a low-power CMOS control IC to provide a total front-end solution in a single package.

Vishay Telefunken's FIR transceivers are available in four package options, including our Baby Face package (TFDU610xE), the standard setting, once

smallest FIR transceiver available on the market. This wide selection provides flexibility for a variety of applications and space constraints. The transceivers are capable of directly interfacing with a wide variety of I/O devices which perform the modulation/demodulation function, including National Semiconductor's PC87338, PC87108 and PC87109, SMC's FDC37C669, FDC37N769 and CAM35C44, and Hitachi's SH3. At a minimum, a current-limiting resistor in series with the infrared emitter and a  $V_{CC}$  bypass capacitor are the only external components required implementing a complete solution.

### **Features**

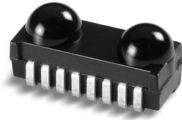
- Compliant to the IrDA physical layer specification (Up to 4 Mbit/s), HP-SIR®, Sharp ASK® and TV Remote Control
- For 3.0 V and 5.0 V Applications
- Operates from 2.6 V to 5.5 V within specification, operational down to 2.4 V
- Low Power Consumption (3 mA Supply Current)
- Power Shutdown Mode (1  $\mu$ A Shutdown Current)
- Four Surface Mount Package Options
  - Universal (9.7  $\times$  4.7  $\times$  4.0 mm)
  - Side View (13.0  $\times$  5.95  $\times$  5.3 mm)
  - Top View (13.0  $\times$  7.6  $\times$  5.95 mm)
  - Dracula (11.2  $\times$  5.6  $\times$  2.2 mm)
- Push-Pull-Receiver Output, grounded in shutdown mode
- High Efficiency Emitter
- Baby Face (Universal) Package Capable of Surface Mount Soldering to Side and Top View Orientation
- Directly Interfaces with Various Super I/O and Controller Devices
- Built-In EMI Protection – No External Shielding Necessary
- Few External Components Required
- Backward Pin to Pin Compatible to all Vishay Telefunken SIR and FIR Infrared Transceivers
- Split power supply, transmitter and receiver can be operated from two power supplies with relaxed requirements, thus saving costs

### **Applications**

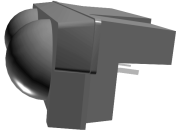
- Notebook Computers, Desktop PCs, Palmtop Computers (Win CE, Palm PC), PDAs
- Digital Still and Video Cameras
- Printers, Fax Machines, Photocopiers, Screen Projectors
- Telecommunication Products (Cellular Phones, Pagers)
- Internet TV Boxes, Video Conferencing Systems
- External Infrared Adapters (Dongles)
- Medical and Industrial Data Collection Devices

## Package Options

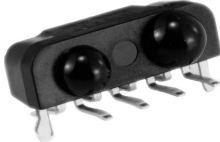
TFDU6102E  
Baby Face (Universal)  
weight 0.20 g



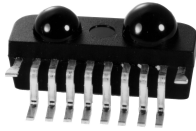
TFDS6402  
Dracula Side View  
weight 0.30 g



TFDS6502E  
Side View  
weight 0.39 g



TFDT6502E  
Top View  
weight 0.39 g



## Ordering Information

| Part Number   | Qty / Reel | Description                                             |
|---------------|------------|---------------------------------------------------------|
| TFDU6102E-TR3 | 1000 pcs   | Oriented in carrier tape for side view surface mounting |
| TFDU6102E-TT3 | 1000 pcs   | Oriented in carrier tape for top view surface mounting  |
| TFDS6402-TR3  | 1000 pcs   | Side View                                               |
| TFDS6502E-TR3 | 750 pcs    | Side View                                               |
| TFDT6502E-TR3 | 750 pcs    | Top View                                                |

## Functional Block Diagram

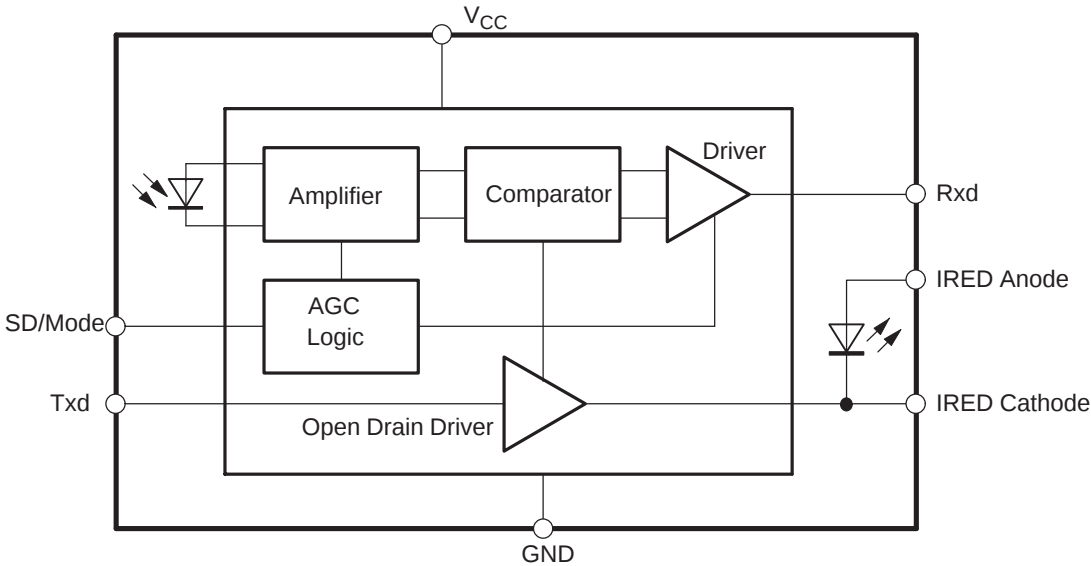


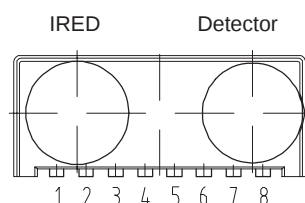
Figure 1. Functional Block Diagram



## Pin Description

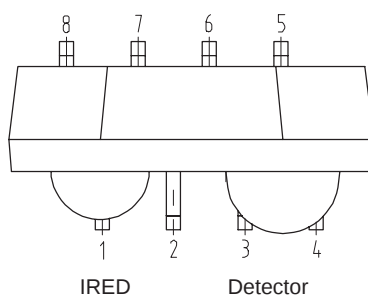
| Pin Number         |            | Function     | Description                                                                                                                                                                                                         | I/O | Active |
|--------------------|------------|--------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|--------|
| "U" and "T" Option | "S" Option |              |                                                                                                                                                                                                                     |     |        |
| 1                  | 8          | IRED Anode   | IRED anode, to be externally connected to $V_{CC}$ through a current control resistor. This pin is allowed to be supplied from an uncontrolled power supply separated from the controlled $V_{CC}$ supply           |     |        |
| 2                  | 1          | IRED Cathode | IRED cathode, internally connected to driver transistor                                                                                                                                                             |     |        |
| 3                  | 7          | Txd          | Transmit Data Input                                                                                                                                                                                                 | I   | HIGH   |
| 4                  | 2          | Rxd          | Received Data Output, push-pull CMOS driver output capable of driving a standard CMOS or TTL load. No external pull-up or pull-down resistor is required.<br><b>Pin is floating when device is in shutdown mode</b> | O   | LOW    |
| 5                  | 6          | SD/Mode      | Shutdown/ Mode                                                                                                                                                                                                      | I   | HIGH   |
| 6                  | 3          | $V_{CC}$     | Supply Voltage                                                                                                                                                                                                      |     |        |
| 7                  | 5          | Mode         | HIGH: High speed mode;<br>LOW: Low speed mode, SIR only (see chapter "Mode Switching")                                                                                                                              | I   |        |
| 8                  | 4          | GND          | Ground                                                                                                                                                                                                              |     |        |

"U" Option Baby Face (Universal) and Dracula



14885

"S" Option Side View



"T" Option Top View

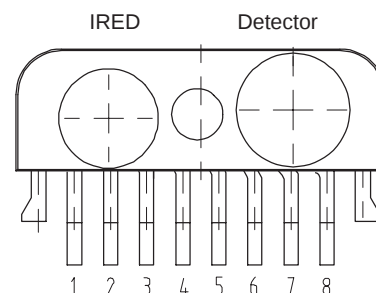


Figure 2. Pinnings

## Absolute Maximum Ratings

Reference point Pin: GND unless otherwise noted.

Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

| Parameters                                                                                           | Test Conditions                                               | Symbol                 | Min.  | Typ. | Max.                   | Unit  |
|------------------------------------------------------------------------------------------------------|---------------------------------------------------------------|------------------------|-------|------|------------------------|-------|
| Supply Voltage Range, Transceiver                                                                    | 0 V < V <sub>CC2</sub> < 6 V                                  | V <sub>CC1</sub>       | – 0.5 |      | 6                      | V     |
| Supply Voltage Range, Transmitter                                                                    | 0 V < V <sub>CC1</sub> < 6 V                                  | V <sub>CC2</sub>       | – 0.5 |      | 6                      | V     |
| Input Currents                                                                                       | For all Pins, Except IRED Anode Pin                           |                        |       |      | 10                     | mA    |
| Output Sinking Current                                                                               |                                                               |                        |       |      | 25                     | mA    |
| Power Dissipation                                                                                    | See Derating Curve                                            | P <sub>D</sub>         |       |      | 350                    | mW    |
| Junction Temperature                                                                                 |                                                               | T <sub>J</sub>         |       |      | 125                    | °C    |
| Ambient Temperature Range (Operating)                                                                |                                                               | T <sub>amb</sub>       | –25   |      | +85                    | °C    |
| Storage Temperature Range                                                                            |                                                               | T <sub>stg</sub>       | –25   |      | +85                    | °C    |
| Soldering Temperature                                                                                | See Recommended Solder Profile (see Figure 11)                |                        |       |      | 240                    | °C    |
| Average Output Current                                                                               |                                                               | I <sub>IRED</sub> (DC) |       |      | 130                    | mA    |
| Repetitive Pulsed Output Current                                                                     | <90 μs, t <sub>on</sub> <20%                                  | I <sub>IRED</sub> (RP) |       |      | 600                    | mA    |
| IRED Anode Voltage                                                                                   |                                                               | V <sub>IRED A</sub>    | – 0.5 |      | 6                      | V     |
| Transmitter Data Input Voltage                                                                       |                                                               | V <sub>Txd</sub>       | – 0.5 |      | V <sub>CC1</sub> + 0.5 | V     |
| Receiver Data Output Voltage                                                                         |                                                               | V <sub>Rxd</sub>       | – 0.5 |      | V <sub>CC1</sub> + 0.5 | V     |
| Virtual Source Size                                                                                  | Method:<br>(1–1/e) encircled energy                           | d                      | 2.5   | 2.8  |                        | mm    |
| Maximum Intensity for Class 1 Operation of IEC825–1 or EN60825–1 (worst case IrDA FIR pulse pattern) | EN60825, 1997, unidirectional operation, worst case test mode |                        |       |      | 320                    | mW/sr |



## Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$ ,  $V_{CC} = 2.6\text{V}$  to  $5.5\text{V}$  unless otherwise noted.

Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

| Parameters                                  | Test Conditions / Pins                                                                                                                  | Symbol   | Min.                | Typ. | Max.     | Unit                           |
|---------------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------|----------|---------------------|------|----------|--------------------------------|
| <b>Transceiver</b>                          |                                                                                                                                         |          |                     |      |          |                                |
| Supply Voltage                              |                                                                                                                                         | $V_{CC}$ | 2.6                 |      | 5.5      | V                              |
| Dynamic Supply Current                      | Receive mode only.<br>In transmit mode, add additional 85 mA (typ) for IRED current                                                     |          |                     |      |          |                                |
|                                             | SD = Low, $E_e = 0\text{ klx}$                                                                                                          | $I_{CC}$ |                     | 3    | 4.5      | mA                             |
|                                             | SD = Low, $E_e = 1\text{ klx}^*)$                                                                                                       | $I_{CC}$ |                     | 3    | 4.5      | mA                             |
| Standby Supply Current                      | SD = High,<br>Mode = Floating,<br>$T = 25^{\circ}\text{C}$ , $E_e = 0\text{ klx}$<br>$T = 25^{\circ}\text{C}$ , $E_e = 1\text{ klx}^*)$ | $I_{SD}$ |                     |      | 1<br>1.5 | $\mu\text{A}$<br>$\mu\text{A}$ |
|                                             | SD = High, $T = 85^{\circ}\text{C}$ ,<br>Mode = Floating,<br>Not Ambient Light<br>Sensitive                                             | $I_{SD}$ |                     |      | 5        | $\mu\text{A}$                  |
| Operating Temperature Range                 |                                                                                                                                         | $T_A$    | -25                 |      | +85      | $^{\circ}\text{C}$             |
| Output Voltage Low                          | $R_{load} = 2.2\text{ k}\Omega$ ,<br>$C_{load} = 15\text{ pF}$                                                                          | $V_{OL}$ |                     | 0.5  | 0.8      | V                              |
| Output Voltage High                         | $R_{load} = 2.2\text{ k}\Omega$ ,<br>$C_{load} = 15\text{ pF}$                                                                          | $V_{OH}$ | $V_{CC}-0.5$        |      |          | V                              |
| Input Voltage Low<br>(Txd, SD/ Mode, Mode)  |                                                                                                                                         | $V_{IL}$ | 0                   |      | 0.8      | V                              |
| Input Voltage High<br>(Txd, SD/ Mode, Mode) | CMOS level **)                                                                                                                          | $V_{IH}$ | $0.9 \times V_{CC}$ |      |          | V                              |
|                                             | TTL level, $V_{CC} \geq 4.5\text{ V}$                                                                                                   | $V_{IH}$ | 2.4                 |      |          | V                              |
| Input Leakage Current<br>(Txd, SD/ Mode)    |                                                                                                                                         | $I_L$    | -10                 |      | +10      | $\mu\text{A}$                  |
| Input Leakage Current,<br>Mode              |                                                                                                                                         | $I_L$    | -80                 |      | +80      | $\mu\text{A}$                  |
| Input Capacitance                           |                                                                                                                                         | $C_I$    |                     |      | 5        | pF                             |

\*) Standard Illuminant A

\*\*) The typical threshold level is between  $0.5 \times V_{CC/2}$  ( $V_{CC} = 3\text{ V}$ ) and  $0.4 \times V_{CC}$  ( $V_{CC} = 5.5\text{ V}$ ) .  
It is recommended to use the specified min/ max values to avoid increased operating current.

## Optoelectronic Characteristics

$T_{amb} = 25^{\circ}\text{C}$ ,  $V_{CC} = 2.6\text{ V}$  to  $5.5\text{ V}$  unless otherwise noted.

Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

| Parameters                                       | Test Conditions                                                                                    | Symbol            | Min. | Typ.     | Max.           | Unit            |
|--------------------------------------------------|----------------------------------------------------------------------------------------------------|-------------------|------|----------|----------------|-----------------|
| <b>Receiver</b>                                  |                                                                                                    |                   |      |          |                |                 |
| Minimum Detection Threshold Irradiance, SIR Mode | TFDS6502E/ TFDT6502E<br>9.6 kbit/s to 115.2 kbit/s<br>$\lambda = 850\text{ nm}$ to $900\text{ nm}$ | $E_e$             |      | 20       | 35             | $\text{mW/m}^2$ |
|                                                  | TFDU6102E, TFDS6402<br>9.6 kbit/s to 115.2 kbit/s<br>$\lambda = 850\text{ nm}$ to $900\text{ nm}$  | $E_e$             |      | 25       | 40             | $\text{mW/m}^2$ |
| Minimum Detection Threshold Irradiance, MIR Mode | TFDS6502E/ TFDT6502E<br>1.152 Mbit/s<br>$\lambda = 850\text{ nm}$ to $900\text{ nm}$               | $E_e$             |      | 50       |                | $\text{mW/m}^2$ |
|                                                  | TFDU6102E, TFDS6402<br>1.152 Mbit/s<br>$\lambda = 850\text{ nm}$ to $900\text{ nm}$                | $E_e$             |      | 65       |                | $\text{mW/m}^2$ |
| Minimum Detection Threshold Irradiance, FIR Mode | TFDS6502E/ TFDT6502E<br>4.0 Mbit/s<br>$\lambda = 850\text{ nm}$ to $900\text{ nm}$                 | $E_e$             |      | 65       | 100            | $\text{mW/m}^2$ |
|                                                  | TFDU6102E, TFDS6402<br>4.0 Mbit/s<br>$\lambda = 850\text{ nm}$ to $900\text{ nm}$                  | $E_e$             |      | 85       | 100            | $\text{mW/m}^2$ |
| Maximum Detection Threshold Irradiance           | $\lambda = 850\text{ nm}$ to $900\text{ nm}$                                                       | $E_e$             | 5    | 10       |                | $\text{kW/m}^2$ |
| Logic LOW Receiver Input Irradiance              |                                                                                                    | $E_e$             | 4    |          |                | $\text{mW/m}^2$ |
| Rise Time of Output Signal—,.,.,,klll            | 10% to 90%, @2.2 k $\Omega$ , 15 pF                                                                | $t_r(\text{Rxd})$ | 10   |          | 40             | ns              |
| Fall Time of Output Signal                       | 90% to 10%, @2.2 k $\Omega$ , 15 pF                                                                | $t_f(\text{Rxd})$ | 10   |          | 40             | ns              |
| Rxd Pulse Width of Output Signal, 50% SIR Mode   | Input pulse length 20 $\mu\text{s}$ , 9.6 kbit/s                                                   | $t_{PW}$          | 1.2  | 10       | 20             | $\mu\text{s}$   |
|                                                  | Input pulse length 1.41 $\mu\text{s}$ , 115.2 kbit/s                                               | $t_{PW}$          | 1.2  |          | 1/2 bit length | $\mu\text{s}$   |
| Rxd Pulse Width of Output Signal, 50% MIR Mode   | Input pulse length 217 ns, 1.152 Mbit/s                                                            | $t_{PW}$          | 110  |          | 260            | ns              |
| Rxd Pulse Width of Output Signal, 50% FIR Mode   | Input pulse length 125 ns, 4.0 Mbit/s                                                              | $t_{PW}$          | 100  |          | 160            | ns              |
|                                                  | Input pulse length 250 ns, 4.0 Mbit/s                                                              | $t_{PW}$          | 200  |          | 290            | ns              |
| Stochastic Jitter, Leading Edge, FIR Mode        | Input Irradiance = 100 $\text{mW/m}^2$ , 4.0 Mbit/s                                                |                   |      | $\pm 10$ |                | ns              |
| Latency                                          |                                                                                                    | $t_L$             |      | 120      | 300            | $\mu\text{s}$   |



## Optoelectronic Characteristics (continued)

$T_{amb} = 25^{\circ}\text{C}$ ,  $V_{CC} = 2.6\text{ V}$  to  $5.5\text{ V}$  unless otherwise noted.

Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

| Parameters                                           | Test Conditions                                                                                                                                                                                | Symbol                     | Min. | Typ.     | Max. | Unit          |
|------------------------------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------------------------|------|----------|------|---------------|
| <b>Transmitter</b>                                   |                                                                                                                                                                                                |                            |      |          |      |               |
| IRED Operating Current                               | $R1^{*}) = 7.2\ \Omega$ , $V_{CC} = 5.0\text{ V}$                                                                                                                                              | $I_D$                      |      | 0.4      | 0.55 | A             |
| Output Radiant Intensity<br>(see Figure 3)           | $V_{CC} = 5.0\text{ V}$ , $\alpha = 0^{\circ}$ , $15^{\circ}$<br>$T_{xd} = \text{High}$ , $S_D = \text{Low}$ , $R1 = 7.2\ \Omega$                                                              | $I_e$                      | 120  | 170      | 350  | mW/sr         |
| Output Radiant Intensity                             | $V_{CC} = 5.0\text{ V}$ , $\alpha = 0^{\circ}$ , $15^{\circ}$<br>$T_{xd} = \text{Low}$ , $S_D = \text{High}$ ,<br>(Receiver is inactive as long as<br>$S_D = \text{High}$ ) $R1 = 7.2\ \Omega$ | $I_e$                      |      |          | 0.04 | mW/sr         |
| Output Radiant Intensity,<br>Angle of Half Intensity |                                                                                                                                                                                                | $\alpha$                   |      | $\pm 24$ |      | $^{\circ}$    |
| Peak – Emission<br>Wavelength                        |                                                                                                                                                                                                | $\lambda_p$                | 880  |          | 900  | nm            |
| Optical Output Pulse<br>Duration                     | Input pulse width 217 ns,<br>1.152 Mbit/s                                                                                                                                                      | $t_{opt}$                  | 207  | 217      | 227  | ns            |
|                                                      | Input pulse width 125 ns,<br>4 Mbit/s                                                                                                                                                          | $t_{opt}$                  | 117  | 125      | 133  | ns            |
|                                                      | Input pulse width 250 ns,<br>4 Mbit/s                                                                                                                                                          | $t_{opt}$                  | 242  | 250      | 258  | ns            |
|                                                      | Input pulse width $t < 80\ \mu\text{s}$<br>Input pulse width $t \geq 80\ \mu\text{s}$                                                                                                          | $t_{opt}$                  |      | $t$      | 80   | $\mu\text{s}$ |
| Optical Rise Time,<br>Fall Time                      |                                                                                                                                                                                                | $t_{ropt}$ ,<br>$t_{fopt}$ | 10   |          | 40   | ns            |
| Optical Overshoot                                    |                                                                                                                                                                                                |                            |      |          | 10   | %             |

\*)  $R1$ : control series resistor for current limitation

## Recommended Circuit Diagram

The only required component for designing an IrDA 1.3 solution using Vishay Telefunken transceivers is a current limiting resistor, R1, to the IRED. However, depending on the entire system design and board layout, additional components may be required (see figure 3).

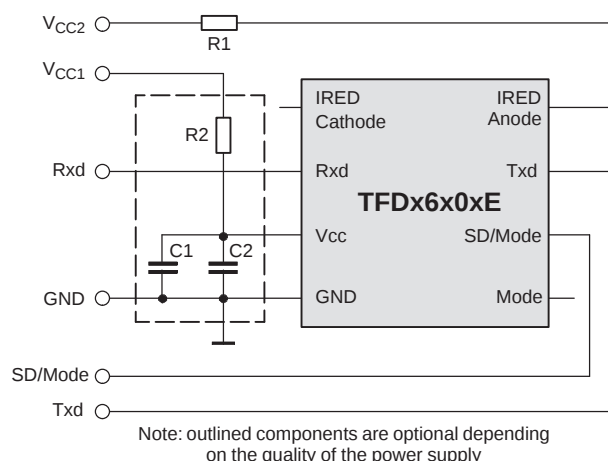


Figure 3. Recommended Application Circuit

Vishay Telefunken transceivers integrate a sensitive receiver and a built-in power driver. The combination of both needs a careful circuit board layout. The use of thin, long, resistive and inductive wiring should be avoided. The inputs (Txd, SD/ Mode) and the output Rxd should be directly (DC) coupled to the I/O circuit.

R1 is used for controlling the current through the IR emitter. For increasing the output power of the IRED, the value of the resistor should be reduced. Similarly, to reduce the output power of the IRED, the value of the resistor should be increased. For typical values of R1 see figure 4. For IrDA compliant operation, a current control resistor of 7.2  $\Omega$  is recommended. For compensating losses of the cosmetic window, reducing that value to 5.6  $\Omega$  is acceptable. The upper drive current limitation is dependent on the duty cycle and is given by the absolute maximum ratings on the data sheet.

R2, C1 and C2 are optional and dependent on the quality of the supply voltage  $V_{CC}$  and injected noise. An unstable power supply with dropping voltage during transmission may reduce sensitivity (and transmission range) of the transceiver.

The placement of these parts is critical. It is strongly recommended to position C2 as near as possible to the transceiver power supply pins. An electrolytic capacitor should be used for C1 while a ceramic capacitor is used for C2.

Table 1. Recommended Application Circuit Components

| Component | Recommended Value                                                                                                                                                                                                                      | Vishay Part Number                               |
|-----------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------------------------------------------------|
| C1        | 4.7 $\mu$ F, Tantalum                                                                                                                                                                                                                  | 293D 475X9 016B 2T                               |
| C2        | 0.1 $\mu$ F, Ceramic                                                                                                                                                                                                                   | VJ 1206 Y 104 J XXMT                             |
| R1        | 5 V supply voltage: 7.2 $\Omega$ , 0.25 W<br>(recommend using<br>two 3.6 $\Omega$ , 0.125 W resistors in series)<br>3.3 V supply voltage: 3.6 $\Omega$ , 0.25 W<br>(recommend using<br>two 1.8 $\Omega$ , 0.125 W resistors in series) | CRCW-1206-3R60-F-RT1<br><br>CRCW-1206-1R80-F-RT1 |
| R2        | 47 $\Omega$ , 0.125 W                                                                                                                                                                                                                  | CRCW-1206-47R0-F-RT1                             |

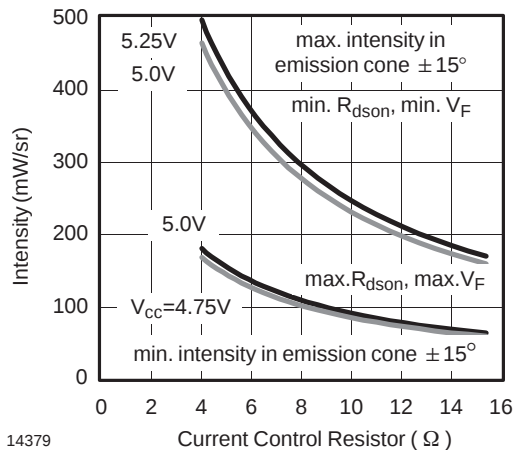


Figure 4. Intensity  $I_e$  vs. Current Control Resistor  $R_1$ , 5 V Applications

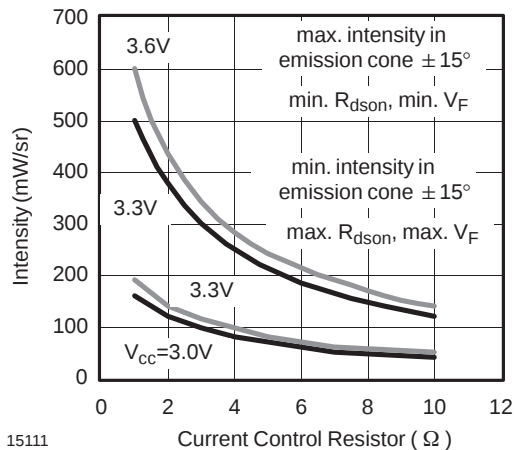


Figure 5. Intensity  $I_e$  vs. Current Control Resistor  $R_1$ , 3 V Applications

In addition, when connecting the described circuit to the power supply, low impedance wiring should be used.

## I/O and Software

In the description, already different I/Os are mentioned. Different combinations are tested and the function verified with the special drivers available from the I/O suppliers. In special cases refer to the I/O manual, the Vishay application notes, or contact directly Vishay Sales, Marketing or Application.

### Control: Differences to TFDx6000 Series

For applications using I/Os from NSC, Winbond and TI no software upgrade is necessary. In combination with the latest SMSC controllers for Microsoft Windows 98® a software upgrade is necessary,

drivers are available from SMSC and Vishay Semiconductor GmbH. This software is intended to work with Windows 95®, too. Alternatively the HP/Sharp settings can be selected. The Microsoft Operating Systems NT 5.0® Beta 2 and Windows 2000® provide Miniport device drivers.

## Mode Switching

The TFDU6102E, TFDS6402, TFDS6502E and TFDT6502E do not power on with a default mode, therefore the data transfer rate has to be set by a programming sequence using the Txd and SD/ Mode inputs as described below or selected by setting the Mode Pin. The Mode Pin can be used to statically set the mode (Mode Pin: LOW: SIR, HIGH: 0.576 Mbit/s to 4.0 Mbit/s). When using the Mode Pin, the standby current may increase to about 50 to 60  $\mu$ A when high or low. If not used or in standby mode, the mode input should float to minimize standby current. The low frequency mode covers speeds up to 115.2 kbit/s. Signals with higher data rates should be detected in the high frequency mode. Lower frequency data can also be received in the high frequency mode but with reduced sensitivity. To switch the transceivers from low frequency mode to the high frequency mode and vice versa, the programming sequences described below are required.

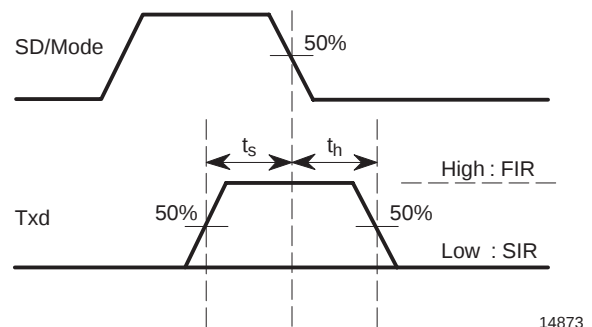


Figure 6. Mode Switching Timing Diagram

### Setting to the High Bandwidth Mode (0.576 Mbit/s to 4.0 Mbit/s)

1. Set SD/MODE input to logic "HIGH".
2. Set Txd input to logic "HIGH". Wait  $t_s \geq 200$  ns.
3. Set SD/MODE to logic "LOW" (this negative edge latches state of Txd, which determines speed setting).
4. After waiting  $t_h \geq 200$  ns Txd can be set to logic "LOW". The hold time of Txd is limited by the maximum allowed pulse length.

Txd is now enabled as normal Txd input for the high bandwidth mode.



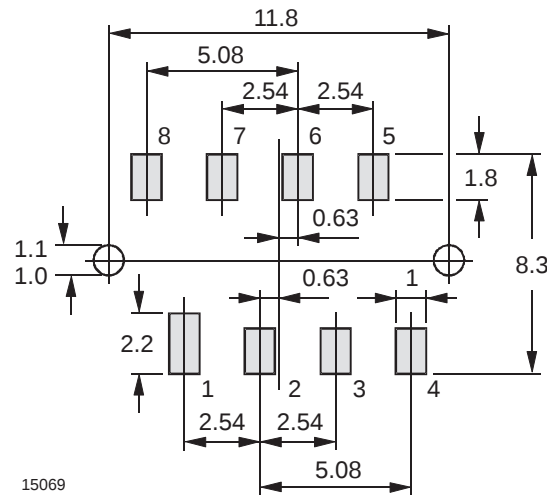


Figure 9. TFDS6502E Side View Package  
Pad 1 is longer to designate Pin 1 connection to transceiver.

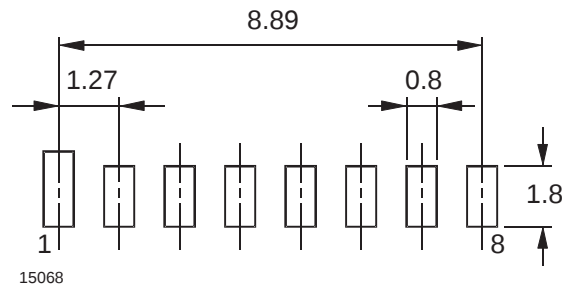


Figure 10. TFDT6502E Top View Package  
Pad 1 is longer to designate Pin 1 connection to transceiver.

Note: Leads of the device should be at least 0.3 mm within the ends of the pads.

## Recommended Solder Profile

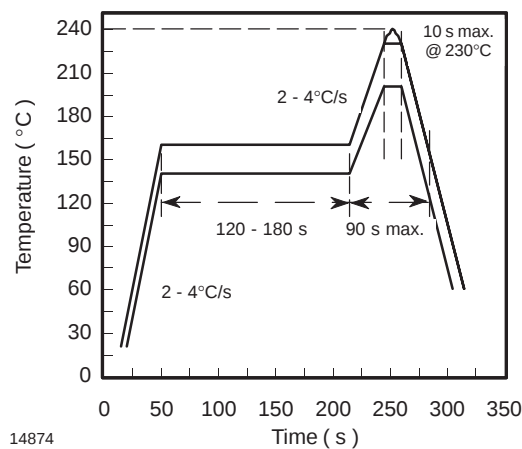


Figure 11. Recommended Solder Profile

## Current Derating Diagram

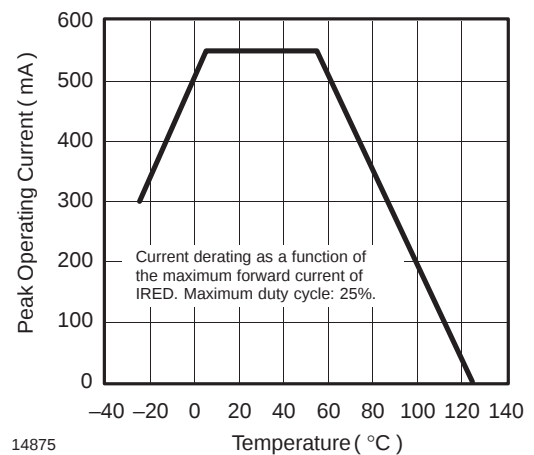
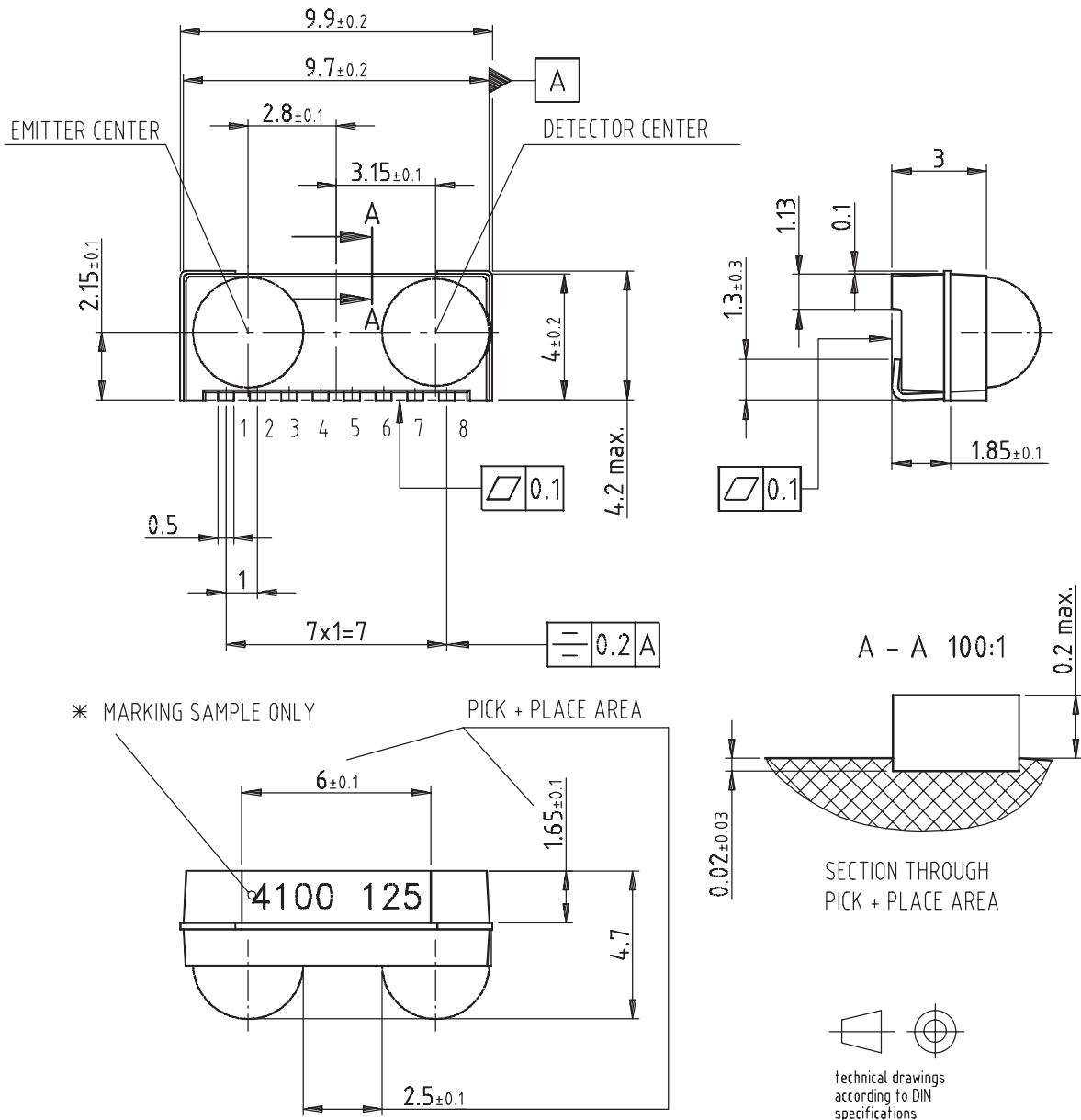


Figure 12. Current Derating Diagram

# TFDU6102E – Baby Face (Universal) Package (Mechanical Dimensions)



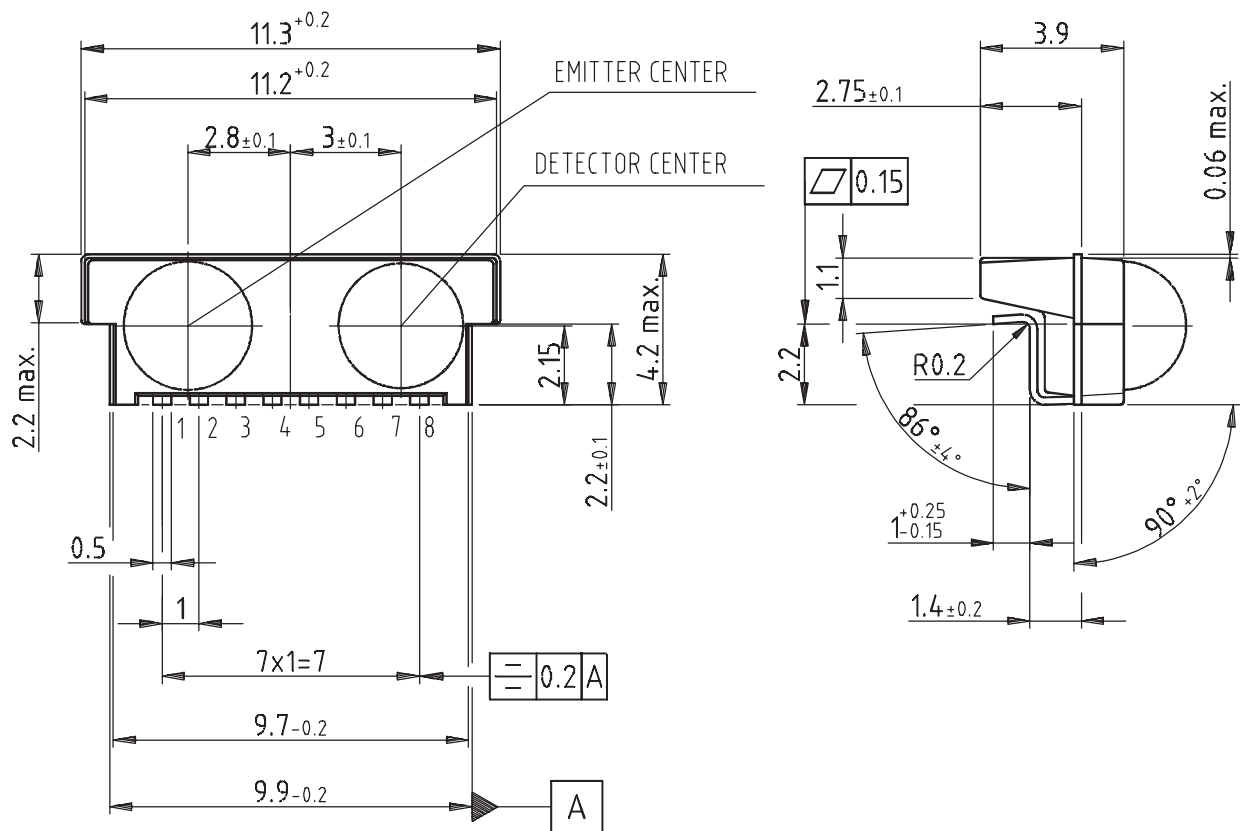
✱ MARKING ORIENTATION  
180 DEGREES ALLOWED

Drawing-No.: 6.550-5148.01-4  
Issue: 11; 29.01.01

12249

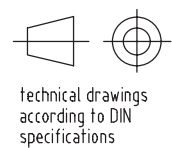
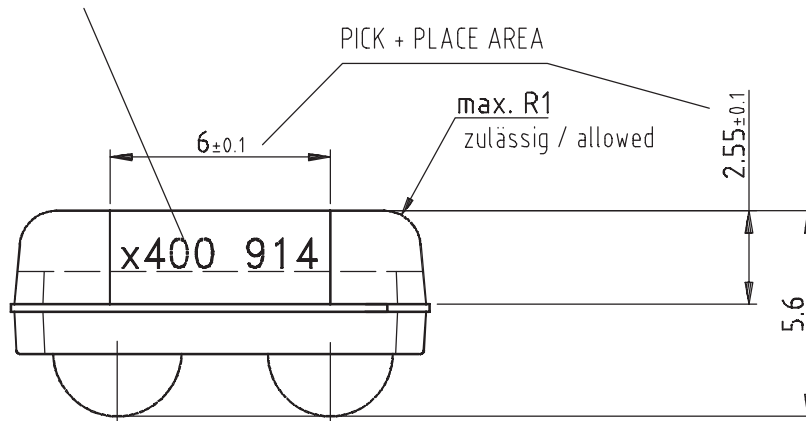


TFDS6402 Package (Mechanical Dimensions)



\* MARKING SAMPLE ONLY

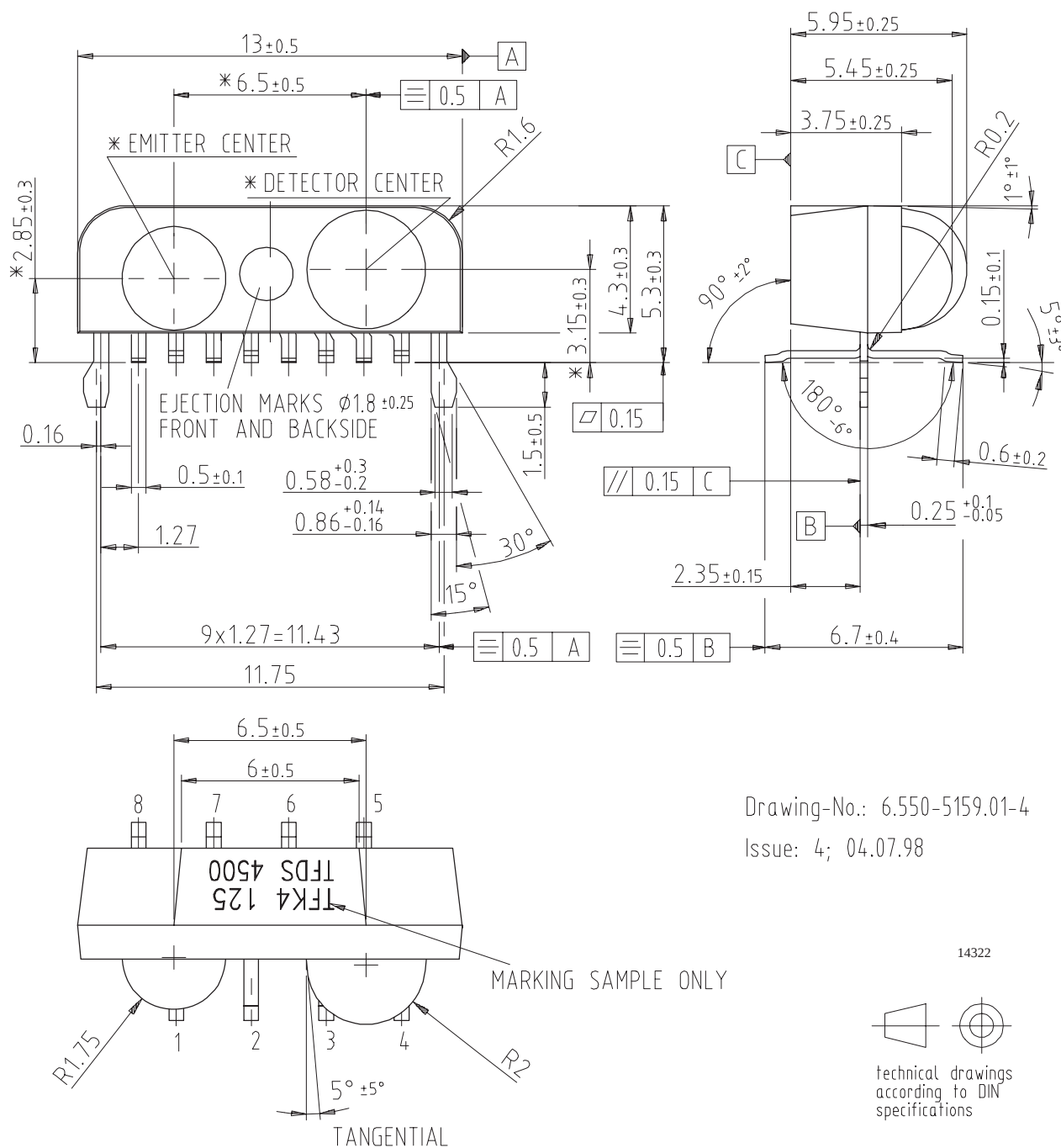
\* MARKING ORIENTATION  
180 DEGREES ALLOWED



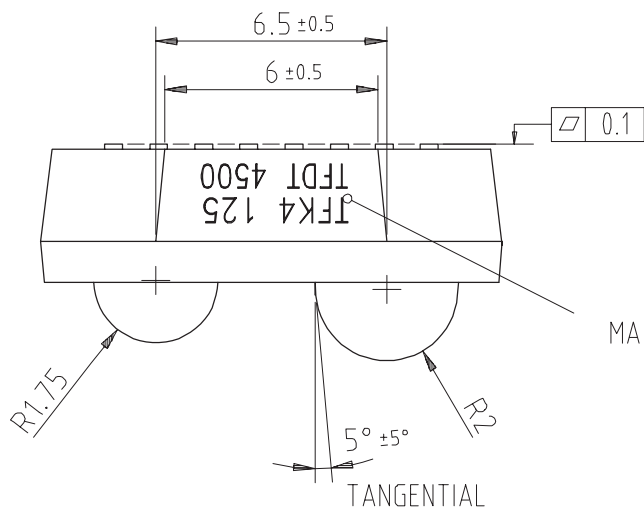
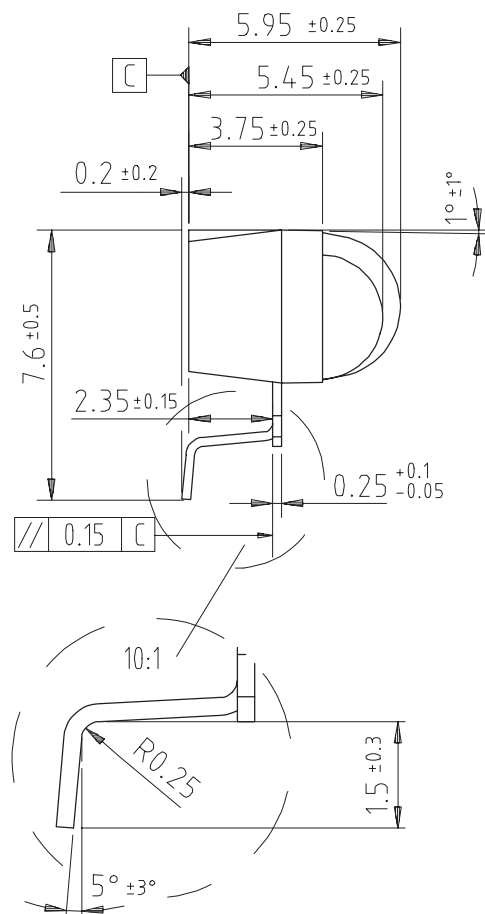
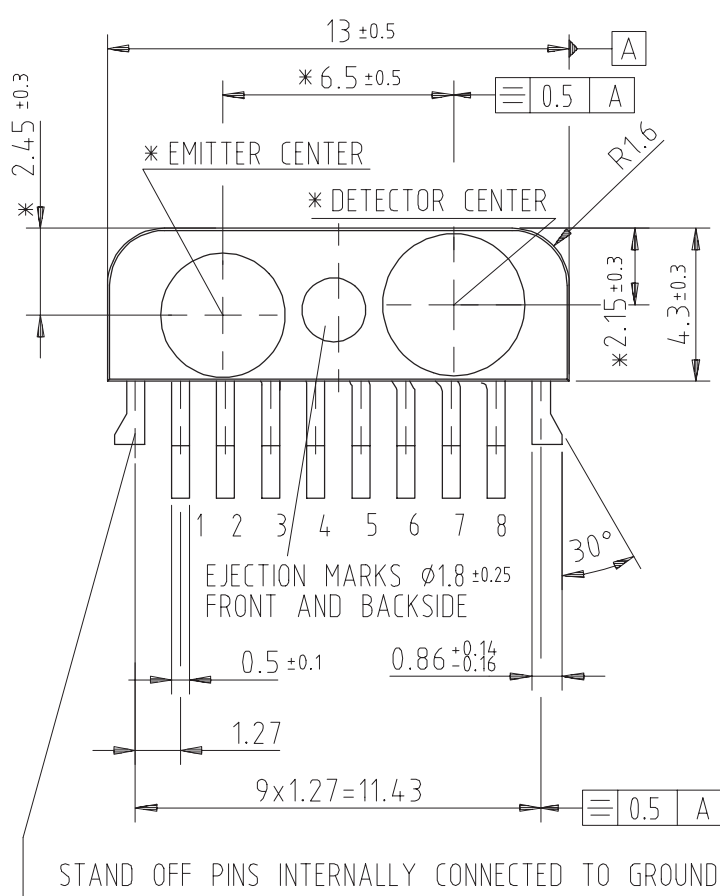
Drawing-No.: 6.550-5203.01-3  
Issue: 2; 03.07.00

15971

### TFDS6502E – Side View Package (Mechanical Dimensions)



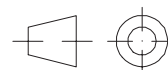
### TFDT6502E – Top View Package (Mechanical Dimensions)



Drawing-No.: 6.550-5160.01-4  
Issue: 4; 28.07.98

MARKING SAMPLE ONLY

14325



technical drawings  
according to DIN  
specifications



### Revision History:

- B1.1, 01/03/1999: New edition for optimized E family. TFDxxx01E – RXD output is grounded when the device is switched to shutdown mode.
- B1.2, 15/03/1999: A clean tri-state version with floating output in shutdown mode was added as 02 version. The output radiant intensity was increased.
- B1.4a, 26/10/1999: TR3 changed to TR4 for 01 types, weight of packages added.
- B1.4b, 22/11/1999: Max. operating current changed from 4.0 mA to 4.5 mA, Dracula package version added, some typos corrected.
- B1.5, 13/10/2000: First typos corrected
- B1.6, 02/11/2000: SMD pad layout tolerances added



## **Ozone Depleting Substances Policy Statement**

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

**Vishay Semiconductor GmbH** has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

**Vishay Semiconductor GmbH** can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

**We reserve the right to make changes to improve technical design and may do so without further notice.**

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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